

DATA SHEET

RZ1214B35Y

NPN microwave power transistor

Product specification
Supersedes data of June 1992

1997 Feb 18

NPN microwave power transistor

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FEATURES

- Interdigitated structure provides high emitter efficiency
- Diffused emitter ballasting resistor providing excellent current sharing and withstanding a high VSWR
- Gold metallization realizes very stable characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input matching ensures good stability and allows an easier design of wideband circuits.

APPLICATIONS

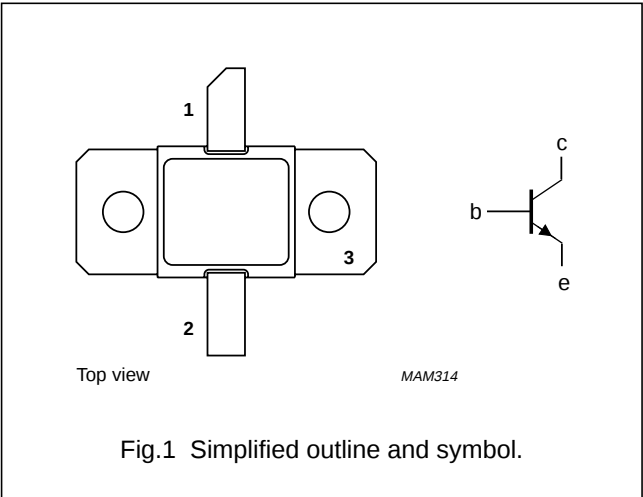
- Common base class-C wideband pulsed power amplifiers for L-band radar applications in the 1.2 to 1.4 GHz band.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT443A metal ceramic flange package with the base connected to the flange.

PINNING - SOT443A

PIN	DESCRIPTION
1	collector
2	emitter
3	base connected to flange



QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common base class-C wideband amplifier.

MODE OF OPERATION	f (GHz)	V _{CC} (V)	P _L (W)	G _p (dB)	η _c (%)	Z _i ; Z _L (Ω)
Class-C; t _p = 150 μs; δ = 5%	1.2 to 1.4	50	≥35	≥7	≥30	see Fig 4

WARNING
Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	65	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0 \Omega$	–	60	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)	$t_p \leq 150 \mu s$; $\delta \leq 5\%$	–	3	A
P_{tot}	total power dissipation	$T_{mb} \leq 75^\circ C$; $t_p \leq 150 \mu s$; $\delta \leq 5\%$	–	125	W
T_{stg}	storage temperature		–65	+200	$^\circ C$
T_j	operating junction temperature		–	200	$^\circ C$
T_{sld}	soldering temperature	at 0.2 mm from the case; $t \leq 10 s$	–	235	$^\circ C$

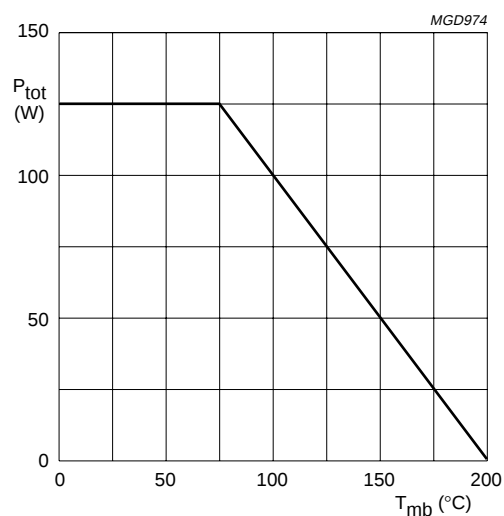
 $t_p = 150 \mu s$; $\delta = 5\%$.

Fig. 2 Power derating curve.

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THERMAL CHARACTERISTICS

 $T_j = 75\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting-base		5	K/W
$R_{th\ mb-h}$	thermal resistance from mounting-base to heatsink	note 1	0.2	K/W
$Z_{th\ j-h}$	thermal resistance from junction to heatsink	$t_p = 100\ \mu\text{s}$; $\delta = 10\ \%$; notes 1 and 2	1	K/W

Notes

- See "Mounting recommendations in the General part of handbook SC19a".
- Equivalent thermal impedance under pulsed microwave operating conditions.

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 20\text{ mA}$; $I_E = 0$	65	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 20\text{ mA}$; $R_{BE} = 0$	60	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0$; $I_E = 3\text{ mA}$	3	–	V
I_{CBO}	collector cut-off current	$V_{CB} = 50\text{ V}$; $I_E = 0$	–	2	mA
I_{EBO}	emitter cut-off current	$V_{EB} = 1.5\text{ V}$; $I_C = 0$	–	0.2	mA

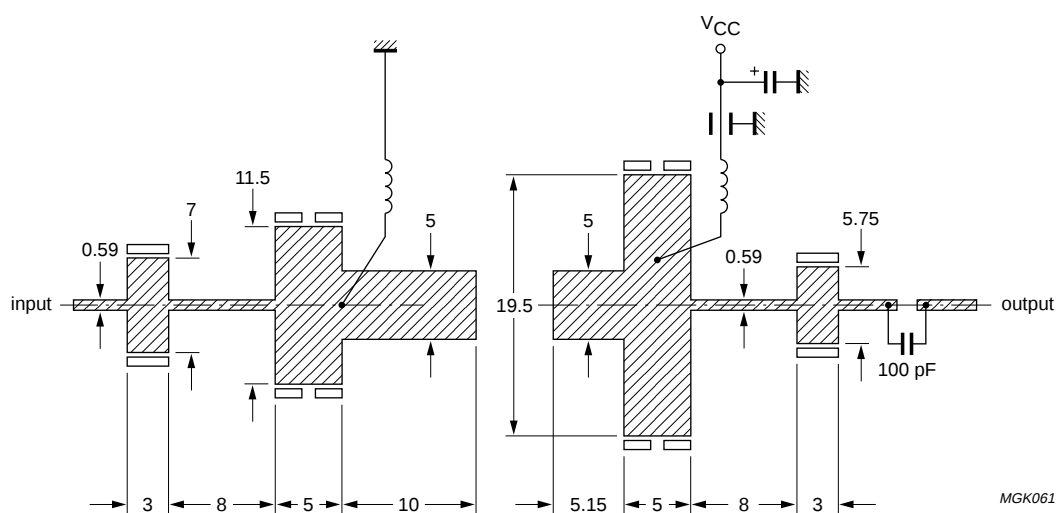
APPLICATION INFORMATION

The transistors are 100% tested under the following conditions

MODE OF OPERATION	CONDITIONS	f (GHz)	V_{CC} (V)	P_L (W)	G_p (dB)	η_c (%)	Z_i ; Z_L (Ω)
Class-C	$t_p = 150\ \mu\text{s}$; $\delta = 5\%$	1.2 to 1.4	50	typ.40; >35	typ.7.8; >7	typ.35; >35	see Fig 4
	$t_p = 300\ \mu\text{s}$; $\delta = 10\%$	1.2 to 1.4	50	typ.40;	typ.7	typ.35	see Fig 4

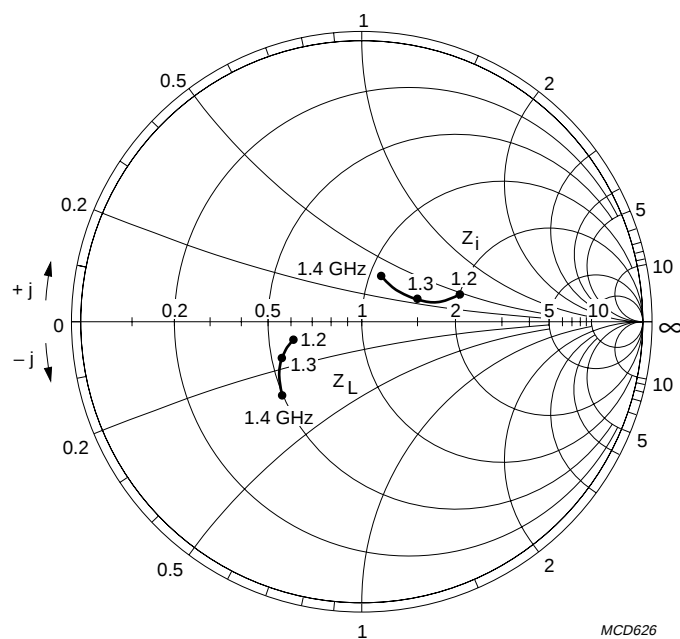
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Dimensions in mm.
 Substrate: Epsilam.
 Thickness: 0.635 mm.
 Permittivity: $\epsilon_r = 10$.

Fig.3 Wideband test circuit for class C operation at 1.2 to 1.4 GHz.



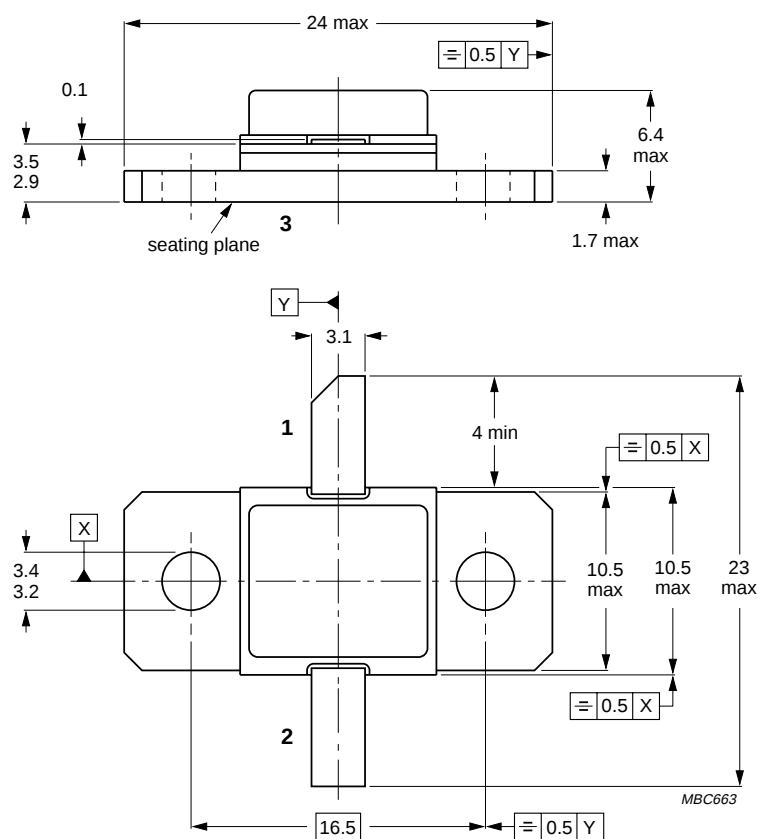
Class C operation; $V_{CE} = 50$ V; $P_L = 35$ W; $Z_0 = 50 \Omega$; $t_p = 150 \mu s$; $\delta = 5\%$.

Fig.4 Input and optimum load impedances as functions of frequency; typical values.

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PACKAGE OUTLINE



Dimensions in mm.
Torque on screw: Max. 0.5 Nm.
Recommended screw: M3.

Fig.5 SOT443A.

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Printed in The Netherlands

127147/00/02/pp8

Date of release: 1997 Feb 18

Document order number: 9397 750 01727

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